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APPLICATION NO.	F	ILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/721,075		11/26/2003	Koichiro Tanaka	0756-7223	7829	
31780	7590	06/29/2005		EXAMINER		
ERIC ROE	BINSON		ELVE, MARIA ALEXANDRA			
PMB 955 21010 SOUTHBANK ST.				ART UNIT	PAPER NUMBER	
POTOMAC FALLS, VA 20165				1725		
				DATE MAILED: 06/29/2005	5	

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Amiliantia				
		Application No.	Applicant(s)				
Office Action Commence		10/721,075 TANAKA, KOIC					
	Office Action Summary	Examiner	Art Unit				
		M. Alexandra Elve	1725				
Period f	The MAILING DATE of this communication app or Reply	sears on the cover sheet w	ith the correspondence address	S			
THE - Exte after - If th - If NO - Failt Any	MAILING DATE OF THIS COMMUNICATION.  MAILING DATE OF THIS COMMUNICATION.  ensions of time may be available under the provisions of 37 CFR 1.1  r SIX (6) MONTHS from the mailing date of this communication.  e period for reply specified above is less than thirty (30) days, a reply  o period for reply is specified above, the maximum statutory period were to reply within the set or extended period for reply will, by statute  reply received by the Office later than three months after the mailing  red patent term adjustment. See 37 CFR 1.704(b).	136(a). In no event, however, may a lifty within the statutory minimum of thir will apply and will expire SIX (6) MON a, cause the application to become Al	reply be timely filed ty (30) days will be considered timely. NTHS from the mailing date of this commun BANDONED (35 U.S.C. § 133).	ication.			
Status	,						
1)[\]	Responsive to communication(s) filed on 19 D	Jecember 2003					
2a)□		s action is non-final.					
3)	,—		ters, prosecution as to the mer	its is			
·	closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.						
Disposit	tion of Claims						
5)□ 6)⊠ 7)□	Claim(s) <u>1-54</u> is/are pending in the application. 4a) Of the above claim(s) is/are withdraw Claim(s) is/are allowed. Claim(s) <u>1-7,10-16,19-25,28-34,37-43 and 46-Claim(s)</u> <u>8-9, 17-18, 26-27, 35-36, 44-45, 53-5Claim(s)</u> are subject to restriction and/o	wn from consideration.  -52 is/are rejected.  54 is/are objected to.					
Applicat	tion Papers						
	The specification is objected to by the Examine	ar					
	The drawing(s) filed on <u>26 November 2003</u> is/a		objected to by the Examiner				
,—	Applicant may not request that any objection to the						
	Replacement drawing sheet(s) including the correct	• • •	` '	121(d).			
11)	The oath or declaration is objected to by the Ex	caminer. Note the attached	d Office Action or form PTO-15	52.			
Priority :	under 35 U.S.C. § 119						
12)⊠ a)	Acknowledgment is made of a claim for foreign All b) Some * c) None of:  1. Certified copies of the priority document: 2. Certified copies of the priority document: 3. Copies of the certified copies of the priority application from the International Bureau See the attached detailed Office action for a list	s have been received. s have been received in A rity documents have been u (PCT Rule 17.2(a)).	application No  received in this National Stag	e			
Attachmen	nt(e)						
1) Notice 2) Notice 3) Infor	ce of References Cited (PTO-892) ce of References Cited (PTO-892) ce of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO-1449 or PTO/SB/08) er No(s)/Mail Date 2/13/04, 1/21/04, 1/2 6	Paper No(: 5) Notice of I	Summary (PTO-413) s)/Mail Date nformal Patent Application (PTO-152) 				

Art Unit: 1725

#### **DETAILED ACTION**

## Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1, 10, 19, 28, 37 & 46 are rejected under 35 U.S.C. 103(a) as being unpatentable over Ogawa et al. (JP 04-124813) in view of Yamazaki et al. (USPN 6,242,292).

Ogawa et al. discloses method and apparatus for manufacturing a semiconductor device. The device is irradiated with continuous wave and pulsed lasers. The types of lasers used are Ar+, CO<sub>2</sub>, Nd-YAG, and so forth. The wavelength used is 308 nm.

Ogawa et al. does not teach the exact order of operations, absorption or the overlap of laser beams.

Yamazaki et al. ('292) discloses producing a semiconductor device using laser beams to anneal and crystallize the substrate. Preliminary irradiation is conducted because the absorptance of laser energy is different for single crystal and polycrystalline materials. Thus amorphous silicon is transformed and then the entire substrate is subjected to annealing. Beam spot size is also indicated in

Art Unit: 1725

the processing. A KrF excimer laser (248 nm) is used. The irradiation is a two stage process and there is overlap of the two laser beams.

It would have been obvious to one of ordinary skill in the art at the time of the invention to note the absorptance or overlap the laser beams, as taught by Yamazaki et al. ('292) it the Ogawa system because absorptance measurement ensures a complete crystalline transformation and hence a quality product, while the overlap of laser beams enhances manufacturing efficiency by decreasing the fabrication time.

The order of operations in an apparatus is matter of design selection. It is well settled that where patentability is predicated upon a change in a condition of prior art process, the change must be at least critical, that is, it must lead to a new and unexpected result. The applicant has the burden of providing such proof of criticality. Note In re Aller e al. 105 USPQ 223.

Claims 2-3, 6-7, 11-12, 15-16, 20-21, 29-30, 33-34, 38-39, 42-43, 47-48 & 51-52 are rejected under 35 U.S.C. 103(a) as being unpatentable over Ogawa et al. and Yamazaki et al. ('292) as stated in the above paragraph and further in view of Kusumoto et al. (USPN 5,953,597).

Ogawa et al. and Yamazaki et al. ('292) do not teach the use of harmonics or all laser types.

Kusumoto et al. discloses the making of a semiconductor device, using laser irradiation. Various lasers are used, such as KrF excimer laser (wavelength

Art Unit: 1725

248 nm), XeCl excimer laser (308 nm), Nd:YAG laser (1064 nm) and a second harmonic component (532 nm) and a third harmonic component (355 nm).

It would have been obvious to one of ordinary skill in the art at the time of the invention to use various lasers and different harmonics, as taught by Kusumoto et al. in the Ogawa et al. and Yamazaki et al. ('292) system because these laser and harmonic types yield tailored irradiation on the semiconductor substrate.

Claims 4-5, 13-14, 22-25, 31-32, 40-41 & 49-50 are rejected under 35 U.S.C. 103(a) as being unpatentable over Ogawa et al. and Yamazaki et al. ('292) as stated in the above paragraph and further in view of Yamazaki et al. (USPN 6,156,997).

Ogawa et al. and Yamazaki et al. ('292) indicate beam spot size in the processing, but do not specifically teach shapes.

Yamazaki et al. ('997) discloses the formation of a semiconductor device, whereby laser beams are overlapped. Beam spots may be square or rectangular.

It would have been obvious to one of ordinary skill in the art at the time of the invention to use different beam spot shapes, as taught by Yamazaki et al. ('997) in the Ogawa et al. and Yamazaki et al. ('292) system because the beam spot type can yield a tailored irradiation on the semiconductor substrate.

Art Unit: 1725

## Allowable Subject Matter

Claims 8-9, 17-18, 26-27, 35-36, 44-45 & 53-54 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

The following is a statement of reasons for the indication of allowable subject matter: the claims as supported by the specification differs from the prior art in that it does not teach the incident angle inequality whereby the angle is greater than or equal to (W1/2d); W1 being the length of the major or minor axis of the beam spot and d being the thickness of the substrate.

#### Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to M. Alexandra Elve whose telephone number is 571-272-1173. The examiner can normally be reached on 6:30-3:00 Monday to Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Dunn can be reached on 571-272-1171. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Art Unit: 1725

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

June 24, 2005.

M. Alexandra Elve

Primary Examiner 1725